

MMBT4401T

NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- BV_{CEO} > 40V
- I_C = 600mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary PNP Type: MMBT2907AT
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.002 grams (Approximate)

SOT523



Top View



Device Schematic



Package Pin Out Configuration

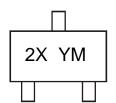
Ordering Information (Note 4)

I	Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	MMBT4401T-7-F	AEC-Q101	2X	7	8	3.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



2X = Product Type Marking Code (See Ordering Information) YM = Date Code Marking Y or \overline{Y} = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Date Code Hoj												
Year	2018	2019	2020	2021	202	22 20)23	2024	2025	2026	2027	2028
Code	F	G	Н		J		K	L	М	N	0	Р
		1									1	1
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	Ic	600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

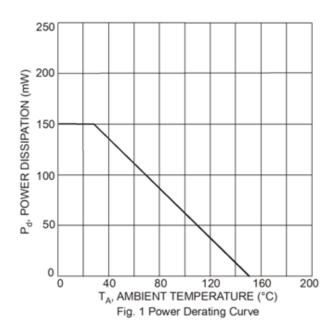
ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information





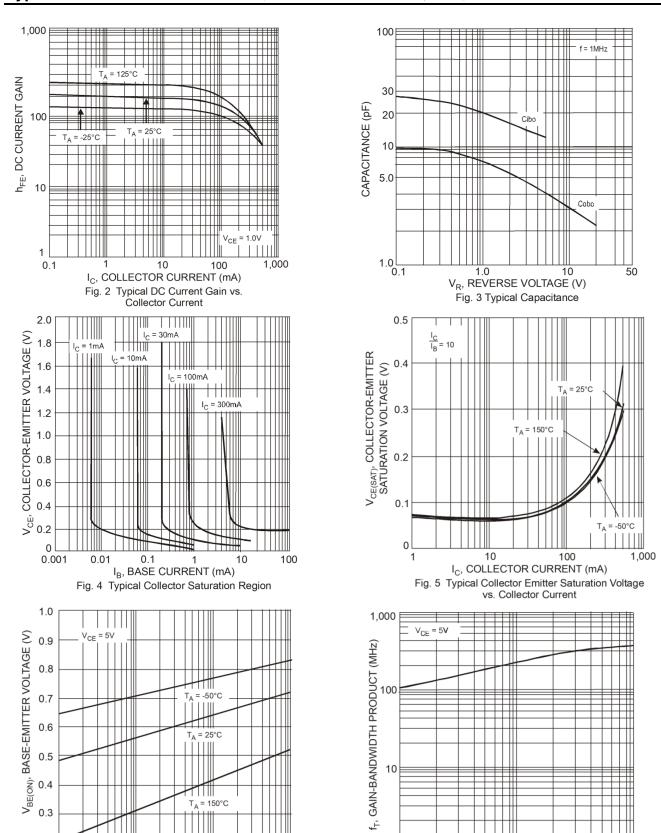
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	_	V	$I_C = 1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
Base Cutoff Current	I_{BL}	_	100	nA	$V_{CE} = 35V$, $V_{EB(OFF)} = 0.4V$
ON CHARACTERISTICS (Note 7)			•		
		20 40	_		$I_C = 100\mu A, V_{CE} = 1V$ $I_C = 1.0mA, V_{CE} = 1V$
DC Current Gain	h _{FE}	80	_	_	Ic = 10mA, V _{CE} = 1V
		100	300		$I_{\rm C} = 150 {\rm mA}, V_{\rm CE} = 1 {\rm V}$
		40	_		I _C = 500mA, V _{CE} = 2V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.4 0.75	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.75	0.95 1.2	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS			l		10 = 0001111 (, 1B = 001111 (
Output Capacitance	$C_{ m obo}$	_	6.5	pF	$V_{CB} = 5V, f = 1.0MHz, I_E = 0$
Input Capacitance	C _{ibo}		30	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$
Input Impedance	h _{ie}	1	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1mA,
Small Signal Current Gain	h _{fe}	75	375	_	f = 1MHz
Output Admittance	h _{oe}	1	30	μS	
Current Gain-Bandwidth Product	f _T	250	_	MHz	$V_{CE} = 20V, I_{C} = 20mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _D	_	15	ns	V _{CC} = 30V, I _C = 150mA,
Rise Time	t _R	_	20	ns	$V_{BE(OFF)} = 2V, I_{B1} = 15mA$
Storage Time	t _S	_	225	ns	V _{CC} = 30V, I _C = 150mA
Fall Time	t _F		30	ns	$I_{B1} = -I_{B2} = 15\text{mA}$

Notes: 7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



10 I_C, COLLECTOR CURRENT (mA) Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current

10

I_C, COLLECTOR CURRENT (mA) Fig. 6 Typical Base-Emitter Voltage vs. Collector Current

0.2

0.1

100

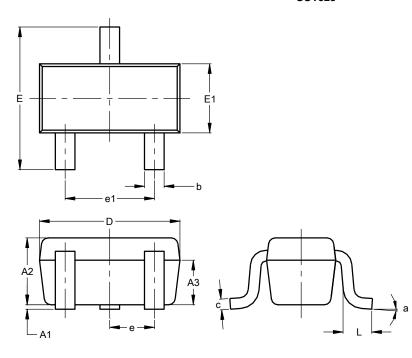
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

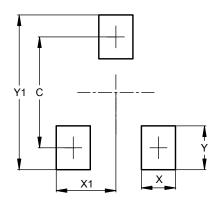


SOT523							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.60	0.80	0.75				
A3	0.45	0.65	0.50				
b	0.15	0.30	0.22				
С	0.10	0.20	0.12				
D	1.50	1.70	1.60				
Е	1.45	1.75	1.60				
E1	0.75	0.85	0.80				
е	e 0.50 BSC						
e1	0.90	1.10	1.00				
L	0.20	0.40	0.33				
а	0°		8°				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value		
Dilliciisiolis	(in mm)		
С	1.29		
Х	0.40		
X1	0.70		
Y	0.51		
Y1	1.80		



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